

(b) Amendments to the Claims

Please cancel claims 6, 7, 10, 28-34 and 39-44 without prejudice or disclaimer. Please amend claim 1 and add new claim 56 as follows. A detailed listing of all the claims that are or were on the application is provided.

--1. (Currently Amended) An exhaust processing process of a processing apparatus for processing a substrate or a film, comprising the steps of:

after processing a substrate or a film, introducing a non-reacted gas and/or a by-product comprising silicon or a compound thereof as a main component into a trap means having therein a filament comprising a high-melting metal material comprising as a main component at least one of tungsten, molybdenum and rhenium;

heating the filament to a temperature from 1400°C to 2200°C; and

processing the non-reacted gas and/or the by-product inside the trap means.

2. (Original) The exhaust processing process according to claim 1, wherein the processing apparatus is an apparatus for forming a deposited film on the substrate by a plasma CVD process.

3. (Original) The exhaust processing process according to claim 1, wherein the processing apparatus is an apparatus for forming a deposited film on the substrate by a thermal CVD process.

4. (Original) The exhaust processing process according to claim 1, wherein the processing apparatus is an apparatus for forming a deposited film on the substrate by a photo CVD process.

5. (Original) The exhaust processing process according to claim 1, wherein the processing apparatus is an apparatus for processing the film by a dry etching process.

6. and 7. (Cancelled)

8. (Original) The exhaust processing process according to claim 1, wherein the configuration of the filament comprises a single linear shape, a plurality of linear shapes or a linear shape wound in spirals.

9. (Previously Presented) The exhaust processing process according to claim 1, wherein the film is a deposited film comprising a silicon-based amorphous or silicon-based microcrystalline material.

10. (Cancelled)

11. (Original) The exhaust processing process according to claim 1, wherein a wall surface of the trap is of a double structure, and an inner wall surface is detachable.

12. - 55 (Cancelled)

56. (New) An exhaust processing process of a processing apparatus for processing a substrate or a film, comprising the steps of:

after processing a substrate or a film, introducing into a trap means a non-reacted gas and/or a by-product comprising silicon or a compound thereof as a main component;

heating the non-reacted gas and/or the by-product to a temperature from 1400°C to 2200°C; and

decomposing the non-reacted gas and/or the by-product inside the trap means.